

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	I _D	-18.0 -14.3	А
	$T_A = +25$ °C $T_A = +70$ °C	ID	-10.6 -8.5	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	-80	Α
Maximum Continuous Body Diode Forward Current (Note 6)		Is	-3.6	Α
Avalanche Current (Note 7) L = 0.3mH		I _{AS}	-17.5	Α
Avalanche Energy (Note 7) L = 0.3mH		E _{AS}	64	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	Б	1.2	W
	T _A = +70°C	P _D	0.9	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	104	°C/W
	t<10s	$R_{\theta JA}$	45	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	PD	1.7	W
	$T_A = +70$ °C	PD	1.1	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	72	°C/W
	t<10s	$R_{\theta JA}$	37	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	13	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

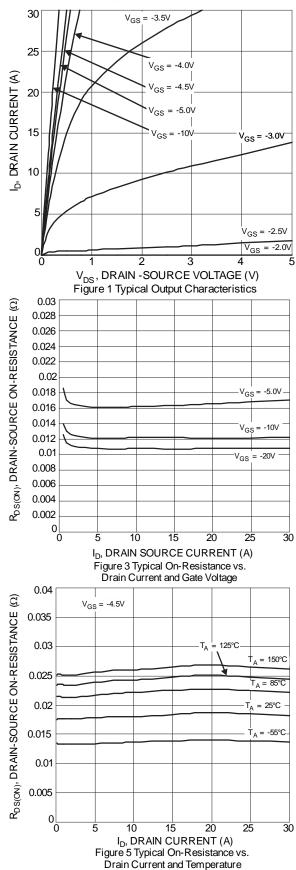
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

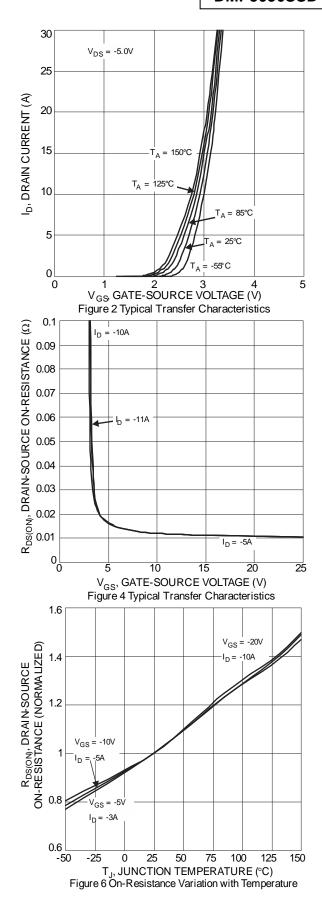
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	1	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	-1.0	-1.7	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D (21)	-	16	20	mΩ	$V_{GS} = -10V, I_D = -9A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	22	29	11122	$V_{GS} = -5V, I_{D} = -7A$	
Diode Forward Voltage	V_{SD}	-	-0.7	-1.0	V	$V_{GS} = 0V$, $I_S = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	1931	-	рF	151/1/	
Output Capacitance	Coss	-	226	-	рF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	168	1	рF	1 = 1.000112	
Gate Resistance	R_{g}	-	10.9	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at V _{GS} = -5V	Q_{g}	-	8.8	-	nC	$V_{DS} = -15V, I_{D} = -10A$	
Total Gate Charge at V _{GS} = -10V	Q_{g}	-	16.5	-	nC		
Gate-Source Charge	Q _{gs}	=	2.6	-	nC	$V_{DS} = -15V, I_{D} = -10A$	
Gate-Drain Charge	Q_{gd}	-	3.6	-	nC	1	
Turn-On Delay Time	t _{D(on)}	=	8.2	-	ns		
Turn-On Rise Time	t _r	-	14	-	ns	$V_{GEN} = -10V, V_{DD} = -15V,$	
Turn-Off Delay Time	t _{D(off)}	-	65	-	ns	$R_{GEN} = 3\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _f	-	31.6	-	ns		

Notes:

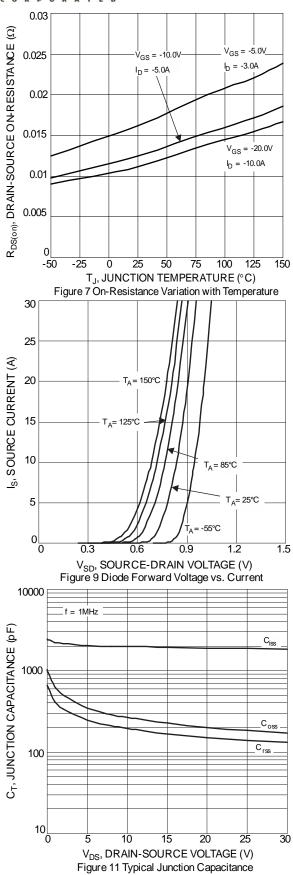
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. IAs and EAs rating are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

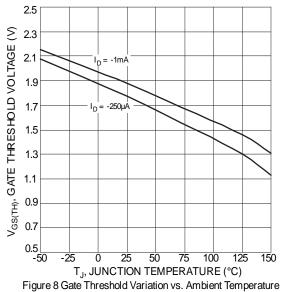


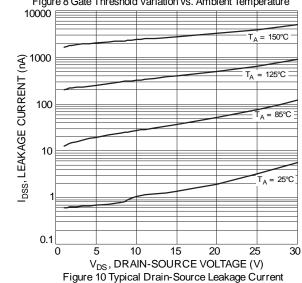


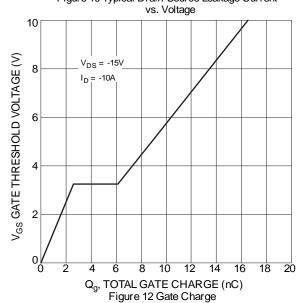




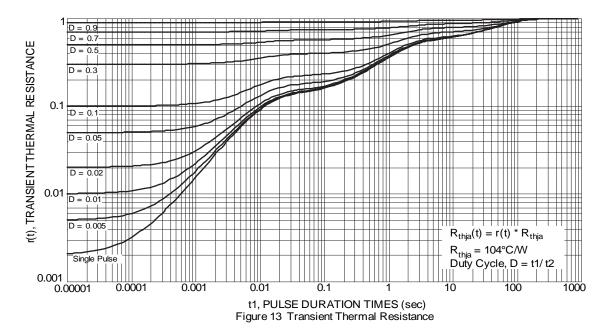






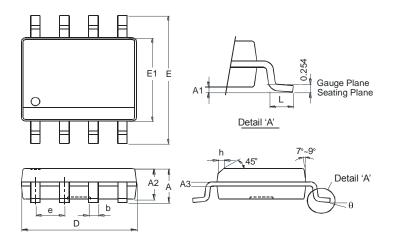






Package Outline Dimensions

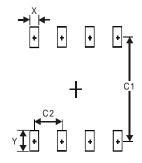
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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